

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Reissue patent application of :

Oh-Sung SONG et al. : **BOX REISSUE**

Serial No. (new)¹ :

Filed June 30, 2003 :

METHOD FOR FABRICATING MOS SEMICONDUCTOR DEVICE HAVING SALICIDE REGION
AND LDD REGION

**AMENDMENT ACCOMPANING
REISSUE APPLICATION**

Honorable Commissioner For Patents
Washington, D.C. 20231

Sir:

Concurrently with the filing of the above-identified reissue application, the
following amendments and remarks are submitted:

In the Claims

Kindly add the following new Claims 9-17:

9. (New) A method for fabricating a metal oxide semiconductor (MOS) transistor,
comprising:

¹ This is a reissue application of U.S. Patent No. 6,255,181 B1, issued July 3, 2001.